

251 North Avenue West, 2nd Floor
Westfield, NJ 07090

13164 Lazy Glen Lane
Oak Hill, Virginia 20171

Mayer, Fortkort & Williams, PC
Attorneys At Law

FAX RECEIVED

APR 10 2003

TECHNOLOGY CENTER 2800

Fax

To: Assistant Commissioner for Patents **From:** David Bonham
(703) 433-0510

Fax: 703-672-9319 **Total pages:** 11

Phone: **Date:** 4/10/03

Re: In connection with prosecution in Serial. No.
09/881,254, please find enclosed an Amendment
and Response to the final Office Action mailed
February 13, 2003.

Sincerely,

David Bonham

Urgent **For Review** **Please Comment** **Please Reply** **Please Recycle**

PRIVACY AND CONFIDENTIALITY NOTICE

The information contained in this communication is confidential and may be legally privileged. It is intended solely for the use of the individual or entity to whom it is addressed and others authorized to receive it. If you are not the intended recipient, you are hereby notified that any disclosure, copying, distribution or taking of any action in reliance on the contents of this information is strictly prohibited.

If you received this communication in error, please immediately notify us by a collect telephone call to the writer and return the original message and documents to us at the above address via the United States postal service.

Please do Not enter. *[Signature]*
Serial No. 09/881,254

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#10/B
Andt
NIE
J. McMillan
4/16/03

Applicant: Fwu-Iuan Hshich et al.

Serial No.: 09/881,254

Filed: 06/14/2001

Title: SYMMETRIC TRENCH MOSFET DEVICE AND METHOD OF
MAKING SAME

Art Unit: 2826

Examiner: Mondt, Johanees P.

FAX RECEIVED

Docket No.: GS 134

APR 10 2003

VIA FACSIMILE 703-872-9319
Box AF
Assistant Commissioner for Patents
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

AMENDMENT AND RESPONSE

Sir:

Responsive to the outstanding Office Action dated February 13, 2003 in the
above-identified patent application, please enter the following amendments and remarks:

IN THE CLAIMS:

Please amend claims 1 and 14 as follows:

B1
1. (Amended) A trench MOSFET transistor device comprising:

 a drain region of a first conductivity type;
 a body region of a second conductivity type provided over said drain region, said
 drain region and said body region forming a first junction;
 a source region of said first conductivity type provided over said body region, said
 source region and said body region forming a second junction;
 source metal disposed on an upper surface of said source region;